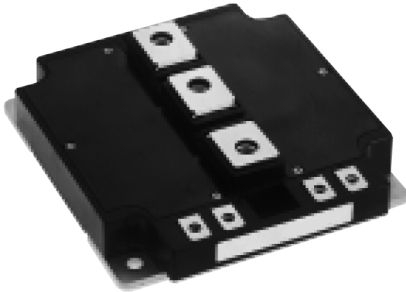


<IGBT Modules>

# CM800DY-24S

**HIGH POWER SWITCHING USE  
INSULATED TYPE**



**dual switch (Half-Bridge)**

Collector current  $I_C$  ..... 7 9 0 A \*  
 Collector-emitter voltage  $V_{CES}$  ..... 1 2 0 0 V  
 Maximum junction temperature  $T_{jmax}$  ..... 1 7 5 °C

- Flat base Type
- Copper base plate
- RoHS Directive compliant
- UL Recognized under UL1557, File E323585

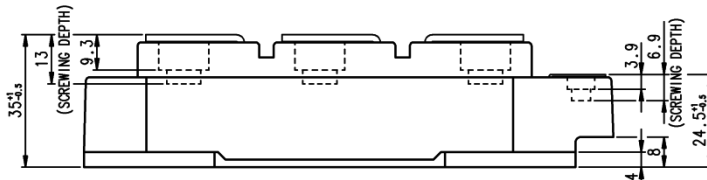
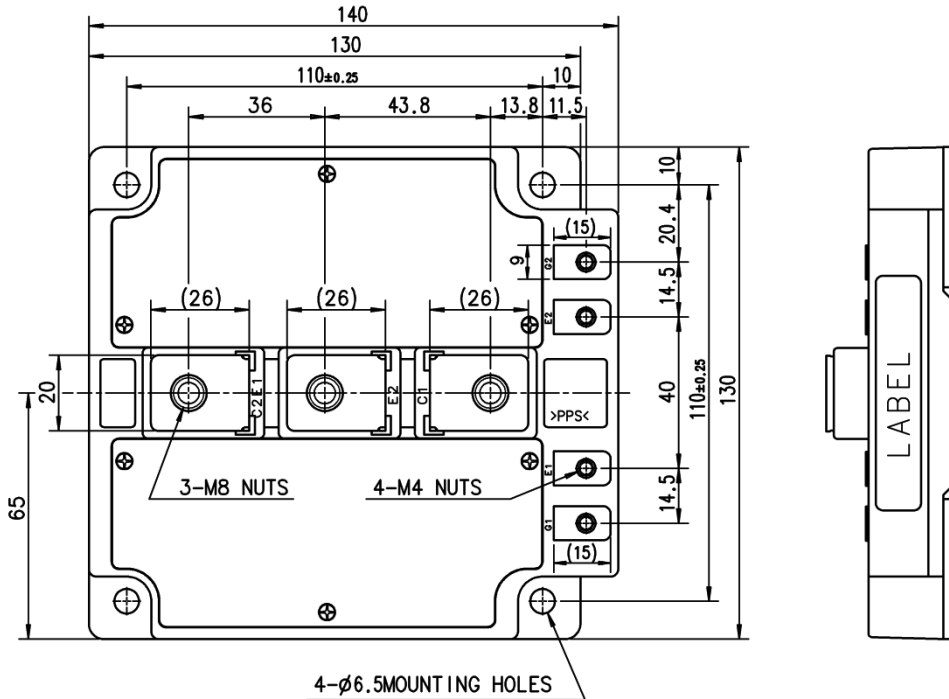
\*. DC current rating is limited by power terminals.

**APPLICATION**

AC Motor Control, Motion/Servo Control, Power supply, etc.

**OUTLINE DRAWING & INTERNAL CONNECTION**

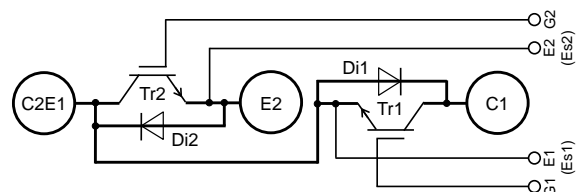
Dimension in mm



Tolerance otherwise specified

Division of Dimension	Tolerance
0.5 to 3	±0.2
over 3 to 6	±0.3
over 6 to 30	±0.5
over 30 to 120	±0.8
over 120 to 400	±1.2

**INTERNAL CONNECTION**



## CM800DY-24S

HIGH POWER SWITCHING USE  
INSULATED TYPEMAXIMUM RATINGS ( $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified)

Symbol	Item	Conditions	Rating	Unit
$V_{CES}$	Collector-emitter voltage	G-E short-circuited	1200	V
$V_{GES}$	Gate-emitter voltage	C-E short-circuited	$\pm 20$	V
$I_C$	Collector current	DC, $T_C=117\text{ }^\circ\text{C}$ (Note2, 4)	790 *	A
		(Note2)	800	
$I_{CRM}$		Pulse, Repetitive (Note3)	1600	
$P_{tot}$	Total power dissipation	$T_C=25\text{ }^\circ\text{C}$ (Note2, 4)	5355	W
$I_E$ (Note1)	Emitter current	DC (Note2)	790 *	A
		(Note2)	800	
$I_{ERM}$ (Note1)		Pulse, Repetitive (Note3)	1600	
$V_{isol}$	Isolation voltage	Terminals to base plate, RMS, $f=60\text{ Hz}$ , AC 1 min	2500	V
$T_{jmax}$	Maximum junction temperature	Instantaneous event (overload)	175	$^\circ\text{C}$
$T_{cmax}$	Maximum case temperature	(Note4)	125	
$T_{jop}$	Operating junction temperature	Continuous operation (under switching)	-40 ~ +150	$^\circ\text{C}$
$T_{stg}$	Storage temperature	-	-40 ~ +125	

ELECTRICAL CHARACTERISTICS ( $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified)

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
$I_{CES}$	Collector-emitter cut-off current	$V_{CE}=V_{CES}$ , G-E short-circuited	-	-	1.0	mA	
$I_{GES}$	Gate-emitter leakage current	$V_{GE}=V_{GES}$ , C-E short-circuited	-	-	0.5	$\mu\text{A}$	
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=80\text{ mA}$ , $V_{CE}=10\text{ V}$	5.4	6.0	6.6	V	
$V_{CESat}$ (Terminal)	Collector-emitter saturation voltage	$I_C=800\text{ A}$ , $V_{GE}=15\text{ V}$ , Refer to fig. of test circuit (Note5)	$T_j=25\text{ }^\circ\text{C}$	-	1.95	2.40	V
			$T_j=125\text{ }^\circ\text{C}$	-	2.25	-	
			$T_j=150\text{ }^\circ\text{C}$	-	2.35	-	
$V_{CESat}$ (Chip)		$I_C=800\text{ A}$ , $V_{GE}=15\text{ V}$ , (Note5)	$T_j=25\text{ }^\circ\text{C}$	-	1.70	2.15	V
			$T_j=125\text{ }^\circ\text{C}$	-	1.90	-	
			$T_j=150\text{ }^\circ\text{C}$	-	1.95	-	
$C_{ies}$	Input capacitance	$V_{CE}=10\text{ V}$ , G-E short-circuited	-	-	80	nF	
$C_{oes}$	Output capacitance		-	-	16		
$C_{res}$	Reverse transfer capacitance		-	-	1.32		
$Q_G$	Gate charge	$V_{CC}=600\text{ V}$ , $I_C=800\text{ A}$ , $V_{GE}=15\text{ V}$	-	1868	-	nC	
$t_{d(on)}$	Turn-on delay time	$V_{CC}=600\text{ V}$ , $I_C=800\text{ A}$ , $V_{GE}=\pm 15\text{ V}$ , $R_G=0\text{ }\Omega$ , Inductive load	-	-	800	ns	
$t_r$	Rise time		-	-	200		
$t_{d(off)}$	Turn-off delay time		-	-	600		
$t_f$	Fall time		-	-	300		
$V_{EC}$ (Note.1) (Terminal)	Emitter-collector voltage	$I_E=800\text{ A}$ , G-E short-circuited, Refer to fig. of test circuit (Note5)	$T_j=25\text{ }^\circ\text{C}$	-	1.85	2.30	V
			$T_j=125\text{ }^\circ\text{C}$	-	1.85	-	
			$T_j=150\text{ }^\circ\text{C}$	-	1.85	-	
$V_{EC}$ (Note.1) (Chip)		$I_E=800\text{ A}$ , G-E short-circuited, (Note5)	$T_j=25\text{ }^\circ\text{C}$	-	1.70	2.15	V
			$T_j=125\text{ }^\circ\text{C}$	-	1.70	-	
			$T_j=150\text{ }^\circ\text{C}$	-	1.70	-	
$t_{rr}$ (Note1)	Reverse recovery time	$V_{CC}=600\text{ V}$ , $I_E=800\text{ A}$ , $V_{GE}=\pm 15\text{ V}$ ,	-	-	300	ns	
$Q_{rr}$ (Note1)	Reverse recovery charge	$R_G=0\text{ }\Omega$ , Inductive load	-	42.8	-	$\mu\text{C}$	
$E_{on}$	Turn-on switching energy per pulse	$V_{CC}=600\text{ V}$ , $I_C=I_E=800\text{ A}$ ,	-	107	-	mJ	
$E_{off}$	Turn-off switching energy per pulse	$V_{GE}=\pm 15\text{ V}$ , $R_G=0\text{ }\Omega$ ,	-	82	-		
$E_{rr}$ (Note1)	Reverse recovery energy per pulse	$T_j=150\text{ }^\circ\text{C}$ , Inductive load	-	71	-	mJ	
$R_{CC'+EE'}$	Internal lead resistance	Main terminals -chip, per switch, $T_C=25\text{ }^\circ\text{C}$ (Note4)	-	-	0.4	m $\Omega$	
$r_g$	Internal gate resistance	Per switch	-	2.45	-	$\Omega$	

# CM800DY-24S

HIGH POWER SWITCHING USE  
INSULATED TYPE

## THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance	Junction to case, per IGBT (Note4)	-	-	28	K/kW
$R_{th(j-c)D}$		Junction to case, per DIODE (Note4)	-	-	45	K/kW
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, per 1/2 module, Thermal grease applied (Note4, 6)	-	15	-	K/kW

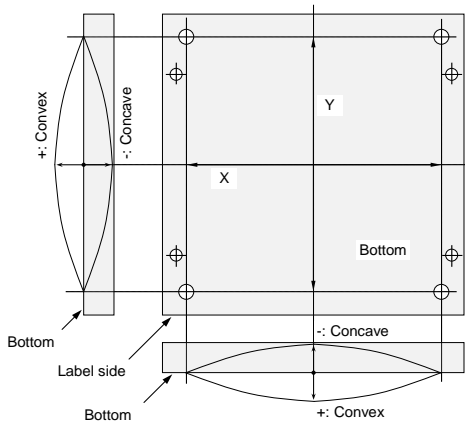
## MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$M_t$	Mounting torque	Main terminals M 8 screw	8.8	9.8	10.8	N·m
		Auxiliary G/Es Terminals M 4 screw	1.3	1.5	1.7	
$M_s$		Mounting to heat sink M 6 screw	3.5	4.0	4.5	N·m
$m$	mass	-	-	1200	-	g
$e_c$	Flatness of base plate	On the centerline X, Y (Note7)	-50	-	+100	$\mu\text{m}$

This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free wheeling diode (FWD).

- Junction temperature ( $T_j$ ) should not increase beyond  $T_{jmax}$  rating.
- Pulse width and repetition rate should be such that the device junction temperature ( $T_j$ ) dose not exceed  $T_{jmax}$  rating.
- Case temperature ( $T_c$ ) and heat sink temperature ( $T_s$ ) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.  
The heat sink thermal resistance should measure just under the chips.
- Pulse width and repetition rate should be such as to cause negligible temperature rise.
- Typical value is measured by using thermally conductive grease of  $\lambda=0.9 \text{ W/(m}\cdot\text{K)}$ .
- Base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.



\*. DC current rating is limited by power terminals.

## RECOMMENDED OPERATING CONDITIONS

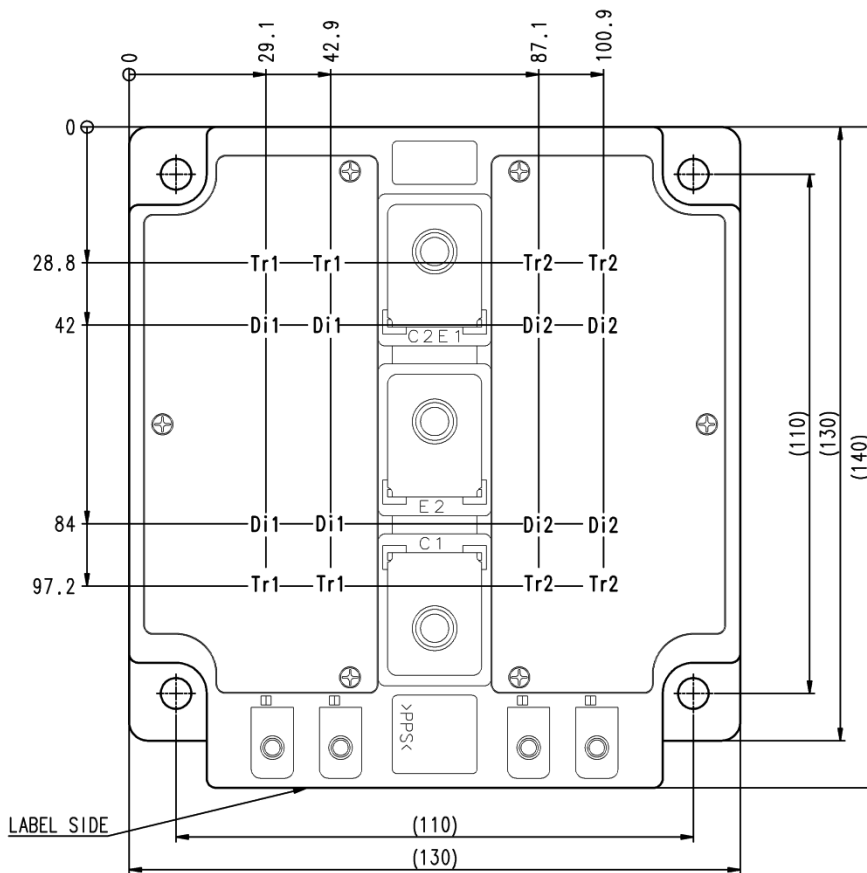
Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{CC}$	(DC) Supply voltage	Applied across C1-E2	-	600	850	V
$V_{GEon}$	Gate (-emitter drive) voltage	Applied across G1-Es1/G2-Es2	13.5	15.0	16.5	V
$R_G$	External gate resistance	Per switch	0	-	5.1	$\Omega$

# CM800DY-24S

HIGH POWER SWITCHING USE  
INSULATED TYPE

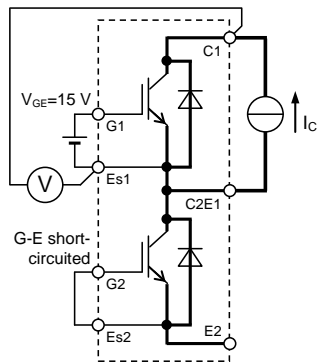
CHIP LOCATION (Top view)

Dimension in mm, tolerance:  $\pm 1$  mm



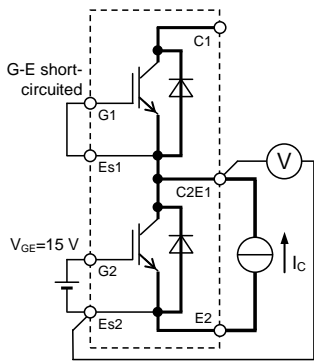
Tr1/Tr2: IGBT, Di1/Di2: DIODE

## TEST CIRCUIT

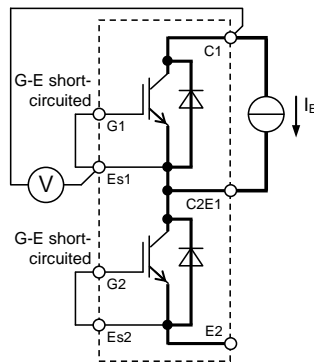


Tr1

$V_{CEsat}$  test circuit

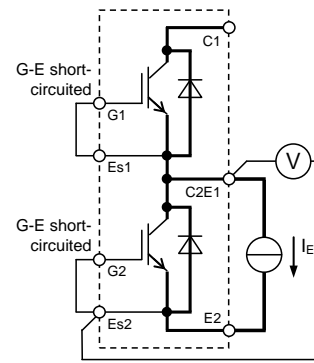


Tr2



Di1

$V_{EC}$  test circuit

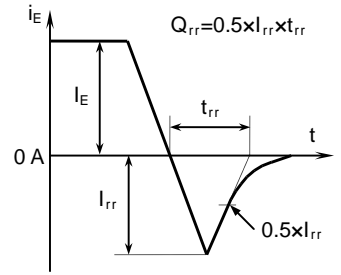
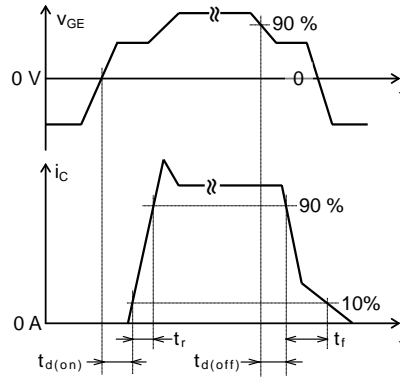
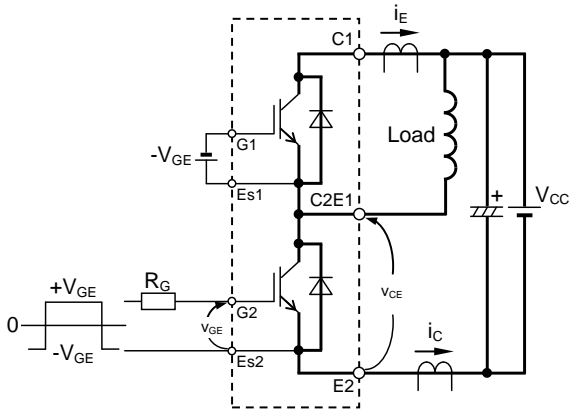


Di2

# CM800DY-24S

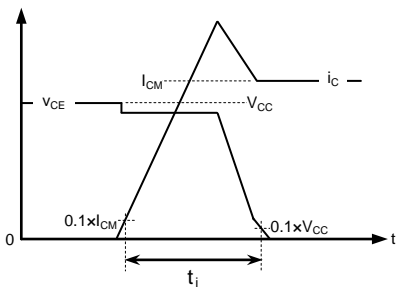
HIGH POWER SWITCHING USE  
INSULATED TYPE

## TEST CIRCUIT AND WAVEFORMS

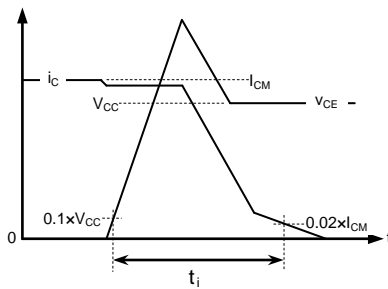


Switching characteristics test circuit and waveforms

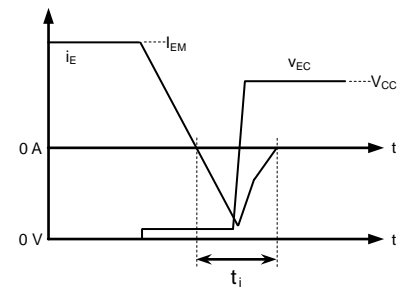
$t_{rr}$ ,  $Q_{rr}$  test waveform



IGBT Turn-on switching energy



IGBT Turn-off switching energy



DIODE Reverse recovery energy

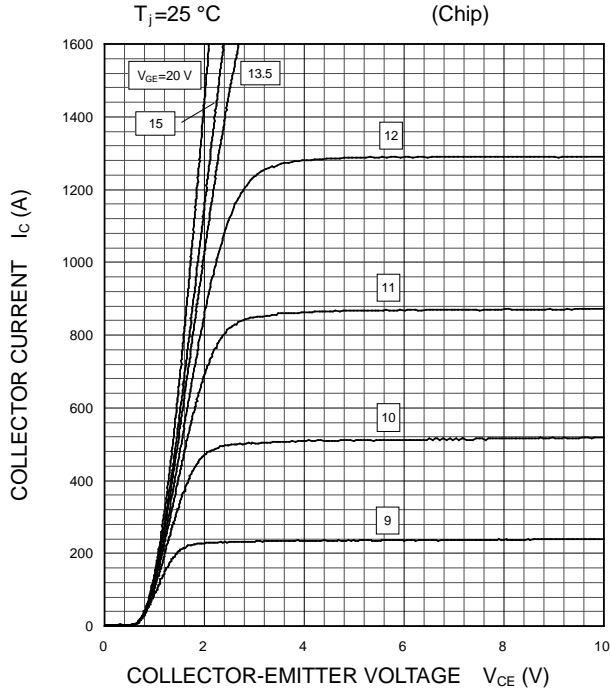
Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

# CM800DY-24S

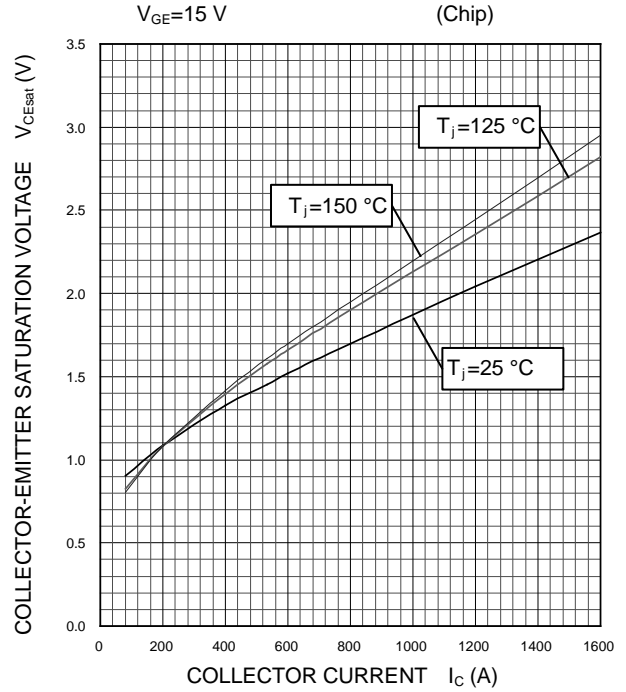
HIGH POWER SWITCHING USE  
INSULATED TYPE

## PERFORMANCE CURVES

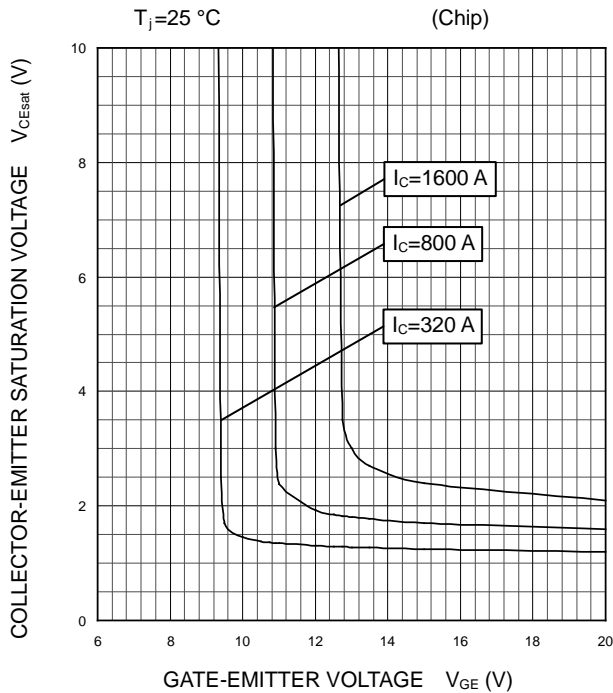
OUTPUT CHARACTERISTICS  
(TYPICAL)



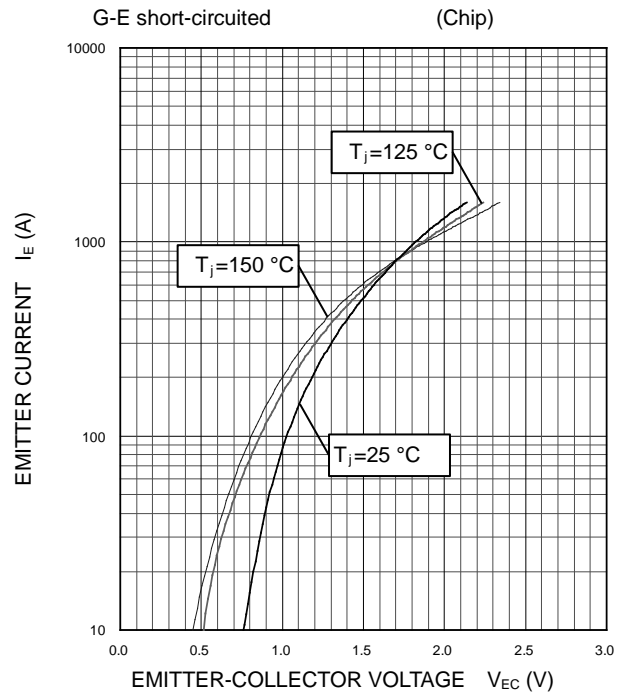
COLLECTOR-EMITTER SATURATION  
VOLTAGE CHARACTERISTICS  
(TYPICAL)



COLLECTOR-EMITTER SATURATION  
VOLTAGE CHARACTERISTICS  
(TYPICAL)



FREE WHEELING DIODE  
FORWARD CHARACTERISTICS  
(TYPICAL)



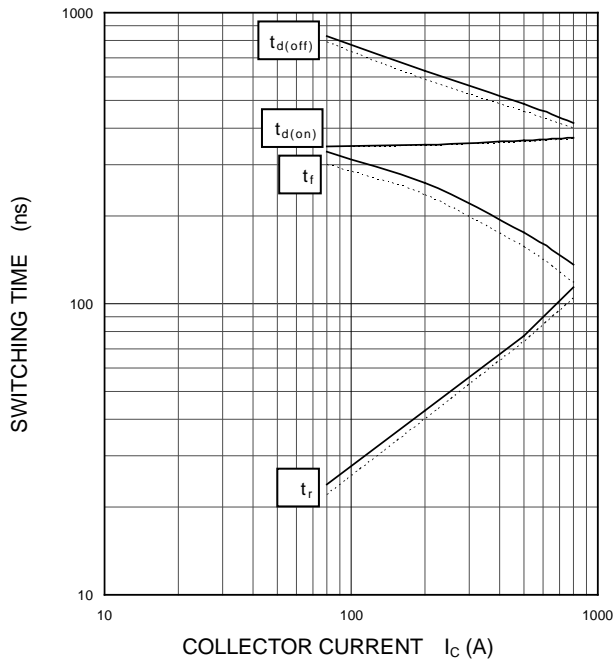
# CM800DY-24S

HIGH POWER SWITCHING USE  
INSULATED TYPE

## PERFORMANCE CURVES

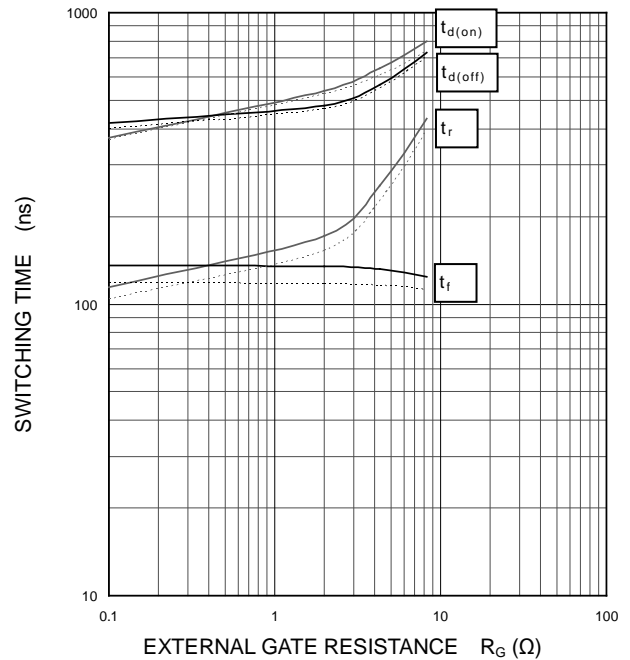
HALF-BRIDGE  
SWITCHING CHARACTERISTICS  
(TYPICAL)

$V_{CC}=600\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $R_G=0\ \Omega$ , INDUCTIVE LOAD  
—:  $T_j=150\text{ }^\circ\text{C}$ , - - - -:  $T_j=125\text{ }^\circ\text{C}$



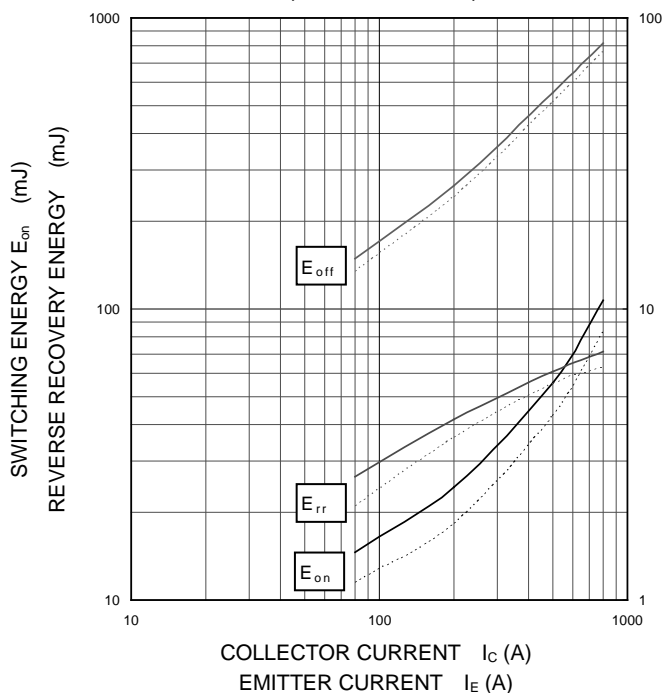
HALF-BRIDGE  
SWITCHING CHARACTERISTICS  
(TYPICAL)

$V_{CC}=600\text{ V}$ ,  $I_C=800\text{ A}$ ,  $V_{GE}=\pm 15\text{ V}$ , INDUCTIVE LOAD  
—:  $T_j=150\text{ }^\circ\text{C}$ , - - - -:  $T_j=125\text{ }^\circ\text{C}$



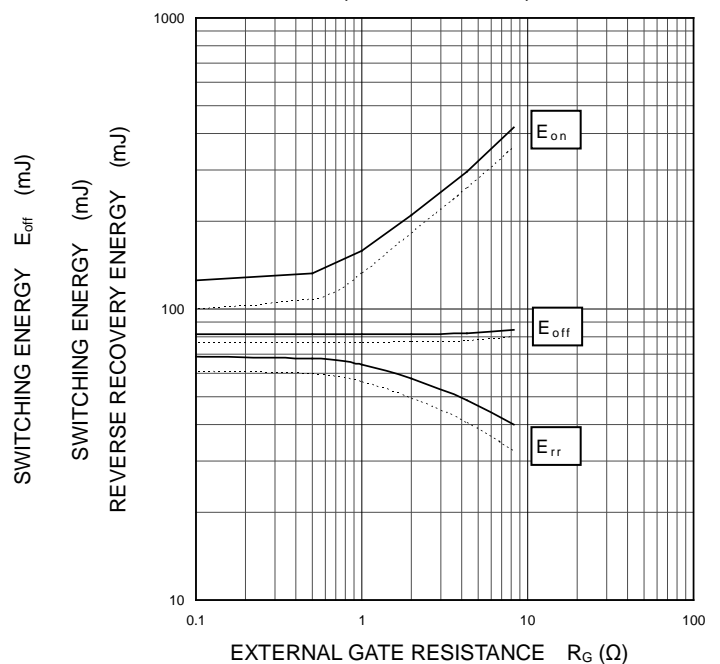
HALF-BRIDGE  
SWITCHING CHARACTERISTICS  
(TYPICAL)

$V_{CC}=600\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $R_G=0\ \Omega$ ,  
INDUCTIVE LOAD, PER PULSE  
—:  $T_j=150\text{ }^\circ\text{C}$ , - - - -:  $T_j=125\text{ }^\circ\text{C}$



HALF-BRIDGE  
SWITCHING CHARACTERISTICS  
(TYPICAL)

$V_{CC}=600\text{ V}$ ,  $I_C/I_E=800\text{ A}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  
INDUCTIVE LOAD, PER PULSE  
—:  $T_j=150\text{ }^\circ\text{C}$ , - - - -:  $T_j=125\text{ }^\circ\text{C}$

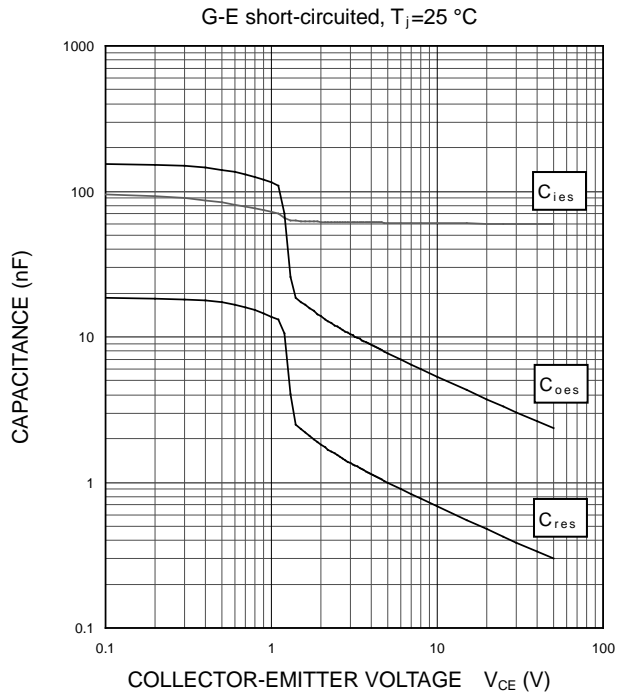


# CM800DY-24S

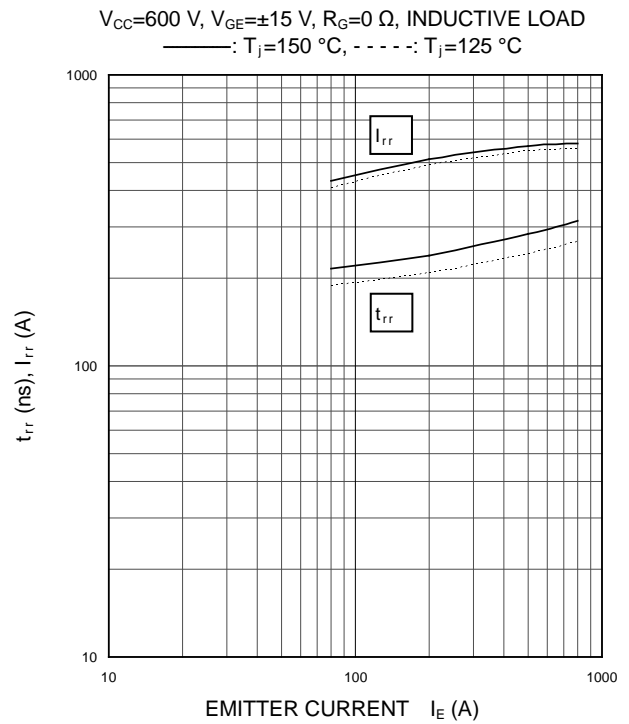
HIGH POWER SWITCHING USE  
INSULATED TYPE

## PERFORMANCE CURVES

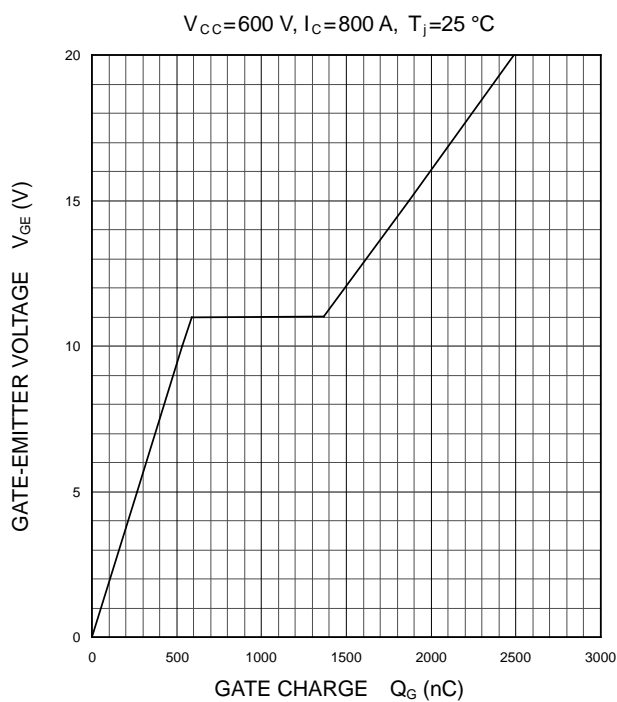
CAPACITANCE CHARACTERISTICS  
(TYPICAL)



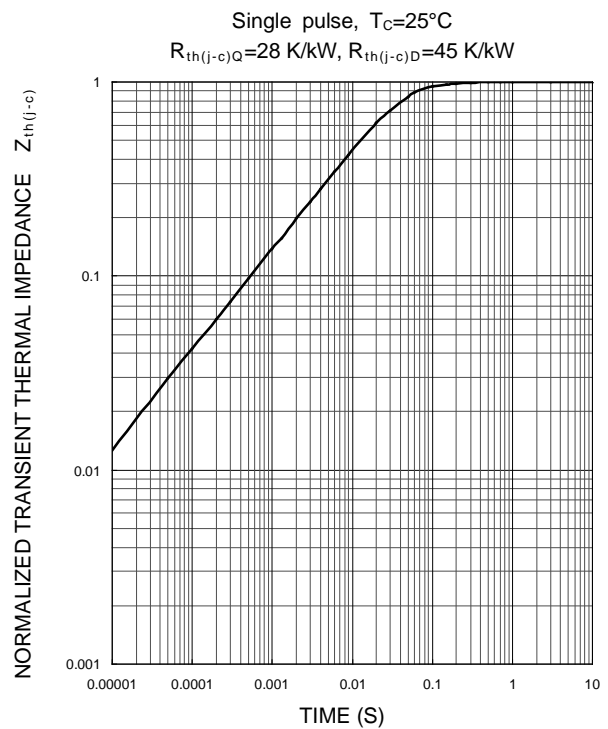
FREE WHEELING DIODE  
REVERSE RECOVERY CHARACTERISTICS  
(TYPICAL)



GATE CHARGE CHARACTERISTICS  
(TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS  
(MAXIMUM)





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